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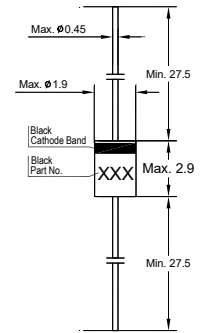
Silicon Epitaxial Planar Switching Diode

Features

- Glass sealed envelope
- High speed
- High reliability

Applications

- High-speed switching



Glass Case DO-34
Dimensions in mm

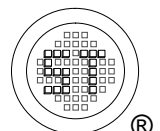
Absolute Maximum Ratings ($T_a = 25^\circ\text{C}$)

Parameter	Symbol	Value	Unit
Peak Reverse Voltage	V_{RM}	90	V
DC Reverse Voltage	V_R	80	V
Average Rectified Forward Current	$I_{F(AV)}$	130	mA
Peak Forward Current	I_{FM}	400	mA
Surge Forward Current at $t < 1$ s	I_{FSM}	600	mA
Power Dissipation	P_{tot}	300	mW
Junction Temperature	T_j	175	$^\circ\text{C}$
Storage Temperature Range	T_{stg}	- 65 to + 175	$^\circ\text{C}$

Thermal Characteristics

Parameter	Symbol	Max.	Unit
Thermal Resistance Junction to Ambient ¹⁾	$R_{\theta JA}$	500	$^\circ\text{C}/\text{W}$

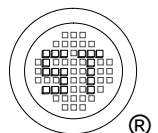
¹⁾ Valid provided that leads at a distance of 8 mm from case are kept at ambient temperature.



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Characteristics at $T_a = 25^\circ\text{C}$

Parameter	Symbol	Min.	Max.	Unit
Reverse Breakdown Voltage at $I_R = 100 \mu\text{A}$	$V_{(BR)R}$	80	-	V
Forward Voltage at $I_F = 100 \text{ mA}$	V_F	-	1.2	V
Reverse Current at $V_R = 80 \text{ V}$	I_R	-	0.5	μA
Capacitance at $V_R = 0.5 \text{ V}$, $f = 1 \text{ MHz}$	C_T	-	1.5	pF
Reverse Recovery Time at $I_F = 10 \text{ mA}$, $V_R = 6 \text{ V}$, $I_{rr} = 0.1 \times I_R$, $R_L = 100 \Omega$	t_{rr}	-	4	ns



Electrical Characteristics Curves

Fig 1. Forward Characteristics

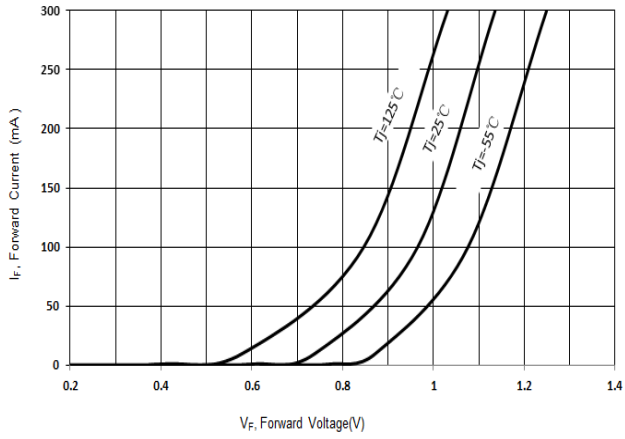


Fig 2. Reverse Characteristics

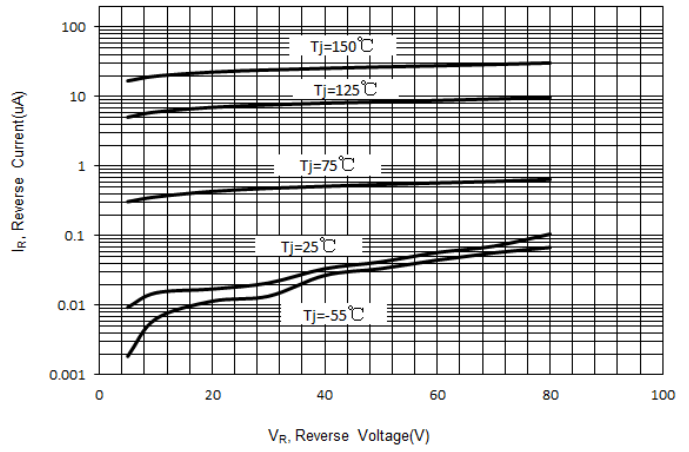


Fig 3. Junction Capacitance

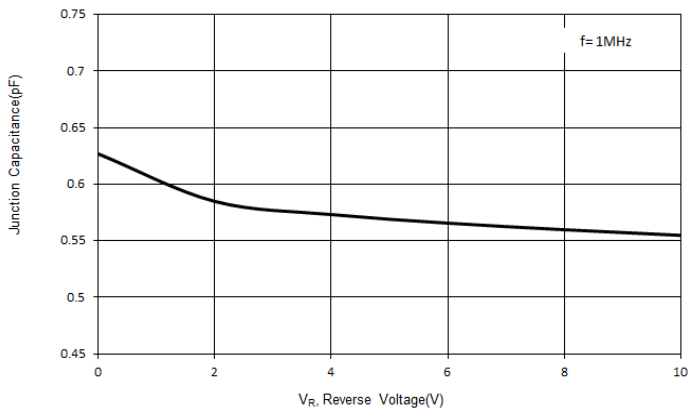


Fig 4. Power Derating Curve

